L Number	Hits	Search Text	DB	Time stamp
1	1013	("257/401").CCLS.	USPAT;	2002/02/01 13:39
-	1020	(251) 101 / 100251	US-PGPUB;	2002,02,01 13.33
			EPO; JPO;	
			DERWENT;	
			IBM TDB	1
2	79	("257/135").CCLS.	USPAT;	2002/02/01 13:39
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
3	124	("257/491").CCLS.	USPAT;	2002/02/01 13:39
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
4	.76	("257/492").CCLS.	USPAT;	2002/02/01 13:39
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
5	83	("257/493").CCLS.	USPAT;	2002/02/01 13:39
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
6	64	("438/212").CCLS.	USPAT;	2002/02/01 13:39
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
7	193	("438/259").CCLS.	USPAT;	2002/02/01 13:39
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
8	1391	("438/270").CCLS.	USPAT;	2002/02/01 13:40
			US-PGPUB;	
			EPO; JPO;	
		<i>'</i>	DERWENT;	
	201	(#A20 (071 H) GGT G	IBM TDB	
9	321	("438/271").CCLS.	USPAT;	2002/02/01 13:40
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	İ
10	221	(#420 /507#)	IBM TDB	0000/00/01 10 10
10	231	("438/587").CCLS.	USPAT;	2002/02/01 13:40
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;]
11	141	("438/588").CCLS.	IBM TDB	2002/02/01 12:40
*	141	(430/300 /.CCD3.	USPAT;	2002/02/01 13:40
			US-PGPUB;	
	ŀ		EPO; JPO; DERWENT;	
			IBM TDB	
12	205	("438/589").CCLS.	USPAT;	2002/02/01 13:40
	203	(400/000 /.0000.	US-PGPUB;	2002/02/01 13:40
			EPO; JPO;	
			1	
1			DERWENT;	
13	0	("L1 or L2 or L3 or L4 or L5 or L6 or L7	IBM TDB	2002/02/01 12 42
10	١	or L8 or L9 or L10").PN.	USPAT;	2002/02/01 13:40
l		OF TO OF TA OF TIO 1. LN.	US-PGPUB;	
1			EPO; JPO;	
			DERWENT;	
			IBM TDB	

14	3400	(("257/401").CCLS.) or (("257/135").CCLS.)	USPAT;	2002/02/01 13:50
		or (("257/491").CCLS.) or	US-PGPUB;	
		(("257/492").CCLS.) or (("257/493").CCLS.)	EPO; JPO;	
		or (("438/212").CCLS.) or	DERWENT;	
		(("438/259").CCLS.) or (("438/270").CCLS.)	IBM TDB	
		or (("438/271").CCLS.) or		
		(("438/587").CCLS.)		
15	274	, , , , , , , , , , , , , , , , , , , ,	USPAT;	2002/02/01 13:53
		(("257/135").CCLS.) or (("257/491").CCLS.)	US-PGPUB;	
		or (("257/492").CCLS.) or	EPO; JPO;	
		(("257/493").CCLS.) or (("438/212").CCLS.)	DERWENT;	
		or (("438/259").CCLS.) or	IBM TDB	
		(("438/270").CCLS.) or (("438/271").CCLS.)		
1		or (("438/587").CCLS.)) and ((groove or		
		trench) near15 insulat\$3 adj2 (layer or		
		film))		
16	329	1 , , , , , , , , , , , , , , , , , , ,	USPAT;	2002/02/01 13:54
•		(("257/135").CCLS.) or (("257/491").CCLS.)	US-PGPUB;	
		or (("257/492").CCLS.) or	EPO; JPO;	
		(("257/493").CCLS.) or (("438/212").CCLS.)	DERWENT;	
		or (("438/259").CCLS.) or	IBM TDB	
		(("438/270").CCLS.) or (("438/271").CCLS.)		
		or (("438/587").CCLS.)) and (groove or		
		trench) adj2 gate		
17	81		USPAT;	2002/02/01 13:56
		(("257/135").CCLS.) or (("257/491").CCLS.)	US-PGPUB;	
		or (("257/492").CCLS.) or	EPO; JPO;	
		(("257/493").CCLS.) or (("438/212").CCLS.)	DERWENT;	
		or (("438/259").CCLS.) or	IBM TDB	
		(("438/270").CCLS.) or (("438/271").CCLS.)		
		or (("438/587").CCLS.)) and (groove or		
		trench) adj2 gate) and base adj2 (region		
1.0	0.1	or layer)	HCDAM.	2002/02/01 14:21
18	81	_ · · · · · · · · · · · · · · · · · · ·	USPAT;	2002/02/01 14:31
		(("257/135").CCLS.) or (("257/491").CCLS.)	US-PGPUB;	
		or (("257/492").CCLS.) or (("438/212").CCLS.)	EPO; JPO; DERWENT;	
		or (("438/259").CCLS.) or	IBM TDB	
		(("438/270").CCLS.) or (("438/271").CCLS.)	I I I I I I I I I I I I I I I I I I I	
		or (("438/587").CCLS.)) and (groove or		
		trench) adj2 gate) and (n-base or p-base	1	
		or p adj base or n adj base or base) adj2		
		(region or layer)		
19	24	hamada.in. and trench	USPAT;	2002/02/01 14:38
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
20	3071	((trench or groove) near3 gate)	EPO; JPO;	2002/02/01 14:39
			DERWENT;	
			IBM TDB	
21	629	((trench or groove) near3 gate) and	EPO; JPO;	2002/02/01 14:40
		conduct\$5 and semiconduct\$5	DERWENT;	
		,,,,	IBM TDB	0000/00/55
22	612	((trench or groove) near3 gate) and	EPO; JPO;	2002/02/01 14:40
		conduct\$5 and semiconduct\$5.ti,ab.	DERWENT;	
23	500	//transh or greate) has 2 sets) ti si	IBM TDB	2002/02/01 14:40
23	598	((trench or groove) near3 gate).ti,ab. and conduct\$5 and semiconduct\$5.ti,ab.	EPO; JPO;	2002/02/01 14:49
		conducts and semiconducts.ti,db.	DERWENT; IBM TDB	
24	120	((trench or groove) near3 gate).ti,ab. and	EPO; JPO;	2002/02/01 15:12
	120	conduct\$5 and semiconduct\$5.ti,ab. and	DERWENT;	2002/02/01 13:12
		connect\$3	IBM TDB	
25	1	5861649.pn.	USPAT	2002/02/01 14:59
26	1	6118150.pn.	EPO; JPO;	2002/02/01 14:33
	_	· · · · ·	DERWENT;	
			IBM TDB	
27	1	6118150.pn.	USPAT	2002/02/01 15:12

-	0	1 = 0.7 + 0.0010. and Dieakdown and avaianche	USPAT;	2002/02/01 13:32
		and low adj on adj resistance	US-PGPUB; EPO; JPO;	
			DERWENT;	
-	0	257/\$5.ccls. and breakdown and low adj on	IBM TDB USPAT;	2001/10/01 07:58
		adj resistance	US-PGPUB;	2001/10/01 07:58
			EPO; JPO;	
			DERWENT; IBM TDB	
-	321		USPAT;	2001/10/01 07:59
		resistance and latch\$3	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	15	257/\$5.ccls. and breakdown and low adj2	USPAT;	2001/10/01 07:59
		resistance and latch\$3 and avalanche and trench	US-PGPUB; EPO; JPO;	
			DERWENT;	,
_	1.5	057 (45	IBM TDB	
_	15	257/\$5.ccls. and breakdown and low adj2 resistance and latch\$3 and avalanche and	USPAT;	2001/10/01 08:10
		trench and power	US-PGPUB; EPO; JPO;	
		•	DERWENT;	
_	0	(257/\$5 cals and baseled.	IBM TDB	
		(257/\$5.ccls. and breakdown and low adj2 resistance and latch\$3 and avalanche and	USPAT;	2001/10/01 08:00
		trench and power) and hamada.in.	US-PGPUB; EPO; JPO;	
			DERWENT;	
_	8	257/\$5.ccls. and breakdown and low adj2	IBM TDB	
		resistance and latch\$3 and avalanche and	USPAT; US-PGPUB;	2001/10/01 08:35
		trench and power and igbt	EPO; JPO;	
			DERWENT;	
-	3	257/\$5.ccls. and breakdown and low adj2	IBM TDB USPAT;	2001/10/01 08:37
		resistance and latch\$3 and avalanche and	US-PGPUB;	2001/10/01 08:3/
		trench and power and igbt and rie	EPO; JPO;	
			DERWENT; IBM TDB	
-	562	vertical near4 mosfet.ti.	USPAT;	2001/10/01 13:15
			US-PGPUB;	1 20120
			EPO; JPO; DERWENT;	
			IBM TDB	
	0	vertical near4 mosfet.ti. and drift adj	USPAT;	2001/10/01 13:15
		drain.ti,ab.	US-PGPUB;	
			EPO; JPO; DERWENT;	
		wortion) manual manager of	IBM TDB	
	U	vertical near4 mosfet.ti. and drift adj2 drain	USPAT;	2001/10/01 13:15
			US-PGPUB; EPO; JPO;	
			DERWENT;	
	7	vertical near4 mosfet.ti. and (drift near4	IBM TDB	0001 (10 15
		drain)	USPAT; US-PGPUB;	2001/10/01 13:15
			EPO; JPO;	
			DERWENT;	
	36	semiconducting adj polymer same	IBM TDB	2001/10/01 16 50
		polyaniline	USPAT; US-PGPUB;	2001/10/01 16:53
			EPO; JPO;	
		,	DERWENT;	
	0	semiconducting adj polymer same	IBM TDB USPAT;	2001/10/01 16:53
	1	polyaniline and 106/\$5.ccls.	US-PGPUB;	2001/10/01 10:53
- 1			EPO; JPO;	ļ
	1	ı	DERWENT;	1

-	356	("257/329").CCLS.		
1		,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	USPAT;	2002/02/01 13:33
	1		US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
-	568	("257/330").CCLS.	IBM TDB	İ
		, , , , , , , , , , , , , , , , , , , ,	USPAT;	2002/02/01 13:33
			US-PGPUB;	1
			EPO; JPO;	
	1	İ	DERWENT;	
_	280	("257/331").CCLs.	IBM TDB	
		, чет, вог у собы.	USPAT;	2002/02/01 13:33
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	æ
-	239	("257/332").CCLs.	IBM TDB	1
		(1077 332):CCB3.	USPAT;	2002/02/01 13:33
	1 '		US-PGPUB;	
	[EPO; JPO;	
			DERWENT;	• [
-	525	("257/341").CCLS.	IBM TDB	
		(= 0.7, 0.12).CCES.	USPAT;	2002/02/01 13:33
	1	•	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
-	284	("257/342").CCLS.	IBM TDB	
	}	, = - , - 12 , . COLD:	USPAT;	2002/02/01 13:33
			US-PGPUB;	
i			EPO; JPO;	ſ
			DERWENT;	ļ
	·		IBM TDB	ļ